

✓IN THE CLAIMS:

✓Please cancel claims 9-11 and 13-19.

✓Please add new claims 20-22:

20. A method of fabricating a polysilicon film,
comprising the steps of:

 providing a substrate;
 depositing an amorphous silicon film on the
substrate by the process of physical vapor deposition;
 depositing a metal catalyst film on the amorphous
silicon film; and

 annealing the amorphous silicon film and the metal
catalyst film to form a crystallized silicon film by pure
metal induced crystallization, wherein the annealing step is
conducted at a temperature greater than 650 °C and for a
time period greater than 200 seconds and less than 800
seconds.

21. The method of claim 1 wherein said metal catalyst
is chosen from the group consisting of aluminum, indium tin
oxide, nickel, cobalt, palladium and germanium.

22. A method of fabricating a polysilicon film,
comprising the steps of:

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providing a substrate;
depositing an amorphous silicon film on the substrate by the process of physical vapor deposition;
after deposition of said amorphous silicon film, depositing a metal catalyst film on selected regions of the amorphous silicon film; and
annealing the amorphous silicon film and the metal catalyst film to form a crystallized silicon film by pure metal induced crystallization in said selected regions.
